MiniSKiiP® 3

SKiiP 39AC12T4V1

Features

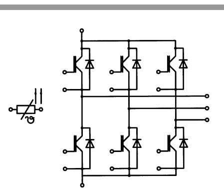
- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Typical Applications*

- Inverter up to 50 kVA
- Typical motor power 30 kW

Remarks

- Max. case temperature limited to T_C=125°C
- Product reliability results valid for T_j≤150°C (recommended $T_{j,op}$=-40...+150°C)
- For short circuit: Soft R_{Goff} recommended
- MiniSKiiP “Technical Explanations” and “Mounting Instructions” are part of the data sheet. Please refer to both documents for further information.



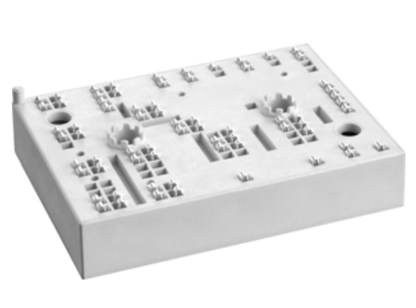
AC

Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
Inverter - IGBT				
V_{CES}	T_j = 25 °C		1200	V
I_C	λ_{paste}=0.8 W/(mK) T_j = 175 °C	T_s = 25 °C	167	A
		T_s = 70 °C	135	A
I_C	λ_{paste}=2.5 W/(mK) T_j = 175 °C	T_s = 25 °C	217	A
		T_s = 70 °C	177	A
I_{Cnom}			150	A
I_{CRM}	I_{CRM} = 3 x I_{Cnom}		450	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 800 V V_{GE} ≤ 15 V V_{CES} ≤ 1200 V	T_j = 150 °C	10	µs
T_j			-40 ... 175	°C
Inverse - Diode				
I_F	λ_{paste}=0.8 W/(mK) T_j = 175 °C	T_s = 25 °C	136	A
		T_s = 70 °C	107	A
I_F	λ_{paste}=2.5 W/(mK) T_j = 175 °C	T_s = 25 °C	163	A
		T_s = 70 °C	130	A
I_{Fnom}			150	A
I_{FRM}	I_{FRM} = 3 x I_{Fnom}		450	A
I_{FSM}	10 ms, sin 180°, T_j = 150 °C		900	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$	$T_{terminal}$ = 80 °C, 20 A per spring		160	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50 Hz, t = 1 min		2500	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
$V_{CE(sat)}$	I_C = 150 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.85	2.10	V
		T_j = 150 °C		2.25	2.45	V
V_{CE0}	chiplevel	T_j = 25 °C		0.80	0.90	V
		T_j = 150 °C		0.70	0.80	V
r_{CE}	V_{GE} = 15 V chiplevel	T_j = 25 °C		7.0	8.0	mΩ
		T_j = 150 °C		10	11	mΩ
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 6 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V, V_{CE} = 1200 V, T_j = 25 °C			0.1	0.3	mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		8.80		nF
C_{oes}		f = 1 MHz		0.58		nF
C_{res}		f = 1 MHz		0.47		nF
Q_G	- 8 V...+ 15 V			850		nC
R_{Gint}	T_j = 25 °C			5.0		Ω
$t_{d(on)}$	V_{CC} = 600 V I_C = 150 A $R_{G\,on}$ = 1 Ω $R_{G\,off}$ = 1 Ω di/dt_{on} = 2840 A/µs di/dt_{off} = 1880 A/µs V_{GE} = +15/-15 V	T_j = 150 °C		165		ns
t_r		T_j = 150 °C		50		ns
E_{on}		T_j = 150 °C		22.5		mJ
$t_{d(off)}$		T_j = 150 °C		390		ns
t_f		T_j = 150 °C		80		ns
E_{off}		T_j = 150 °C		14		mJ
$R_{th(j-s)}$	per IGBT, λ_{paste}=0.8 W/(mK)			0.33		K/W
$R_{th(j-s)}$	per IGBT, λ_{paste}=2.5 W/(mK)			0.21		K/W



MiniSKiiP® 3

SKiiP 39AC12T4V1

Features

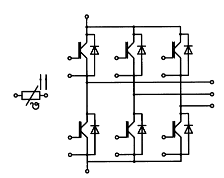
- Trench 4 IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised: File no. E63532

Typical Applications*

- Inverter up to 50 kVA
- Typical motor power 30 kW

Remarks

- Max. case temperature limited to T_C=125°C
- Product reliability results valid for T_j≤150°C (recommended $T_{j,op}$=-40...+150°C)
- For short circuit: Soft R_{Goff} recommended
- MiniSKiiP "Technical Explanations" and "Mounting Instructions" are part of the data sheet. Please refer to both documents for further information.



AC

Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
Inverse - Diode						
$V_F = V_{EC}$	I_F = 150 A V_{GE} = 0 V chiplevel	T_j = 25 °C		2.14	2.46	V
		T_j = 150 °C		2.07	2.38	V
V_{F0}	chiplevel	T_j = 25 °C		1.30	1.50	V
		T_j = 150 °C		0.90	1.10	V
r_F	chiplevel	T_j = 25 °C		5.6	6.4	mΩ
		T_j = 150 °C		7.8	8.5	mΩ
I_{RRM}	I_F = 150 A di/dt$_{off}$ = 4020 A/µs +15/-15 V_{CC} = 600 V	T_j = 150 °C		188		A
Q_{rr}		T_j = 150 °C		27		µC
E_{rr}		T_j = 150 °C		11.4		mJ
$R_{th(j-s)}$	per Diode, λ_{paste}=0.8 W/(mK)			0.52		K/W
$R_{th(j-s)}$	per Diode, λ_{paste}=2.5 W/(mK)			0.39		K/W
Module						
L_{CE}						nH
M_s	to heat sink		2		2.5	Nm
w				82		g
Temperature Sensor						
R_{100}	T_r=100°C (R_{25}=1000Ω)			1670 ± 3%		Ω
R(T)	R(T)=1000Ω[1+A(T-25°C)+B(T-25°C)^2], A = 7.635*10^{-3} °C^{-1}, B = 1.731*10^{-5} °C^{-2}					

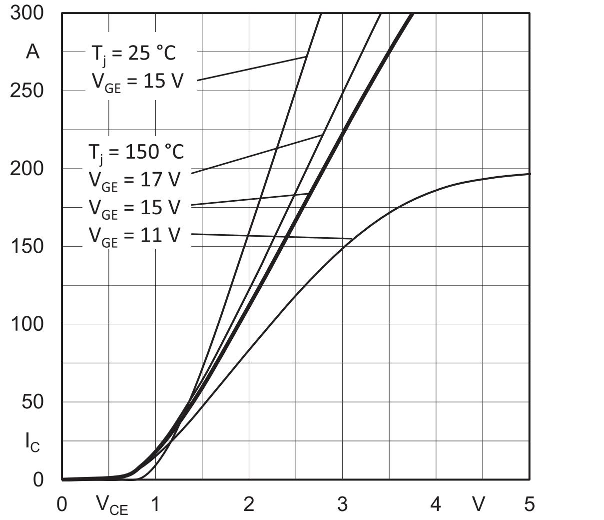


Fig. 1: Typ. output characteristic, inclusive $R_{CC'+EE'}$

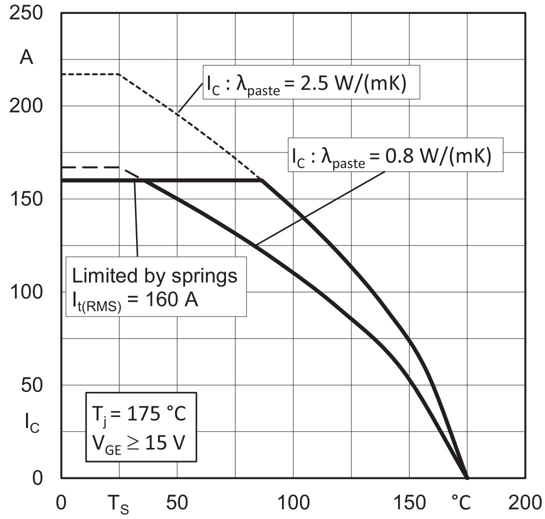


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

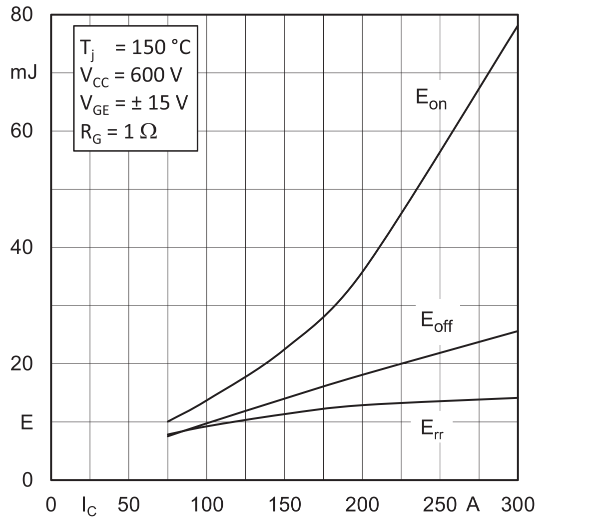


Fig. 3: Typ. turn-on /-off energy = f (I_C)

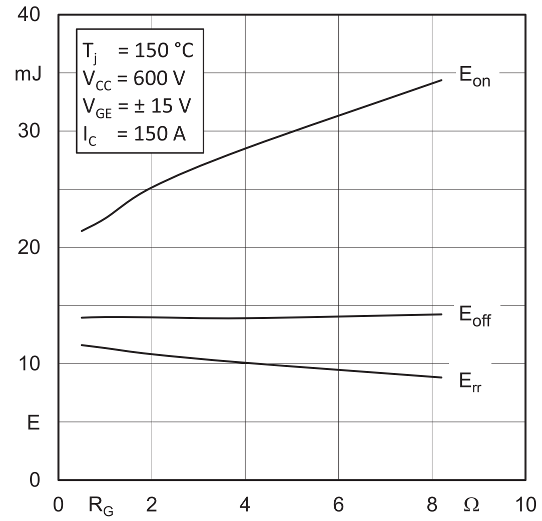


Fig. 4: Typ. turn-on /-off energy = f (R_G)

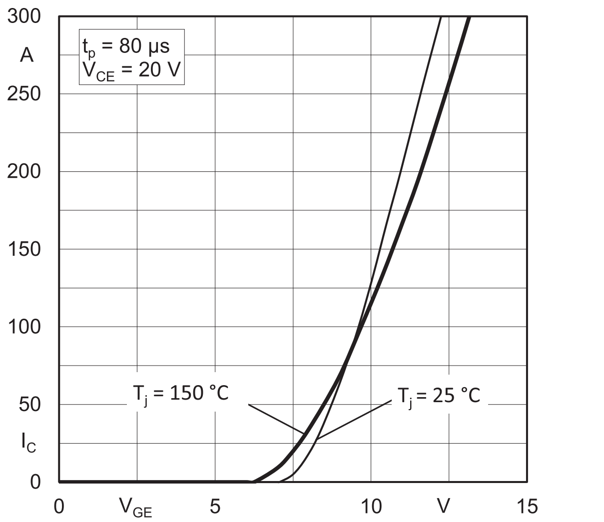


Fig. 5: Typ. transfer characteristic

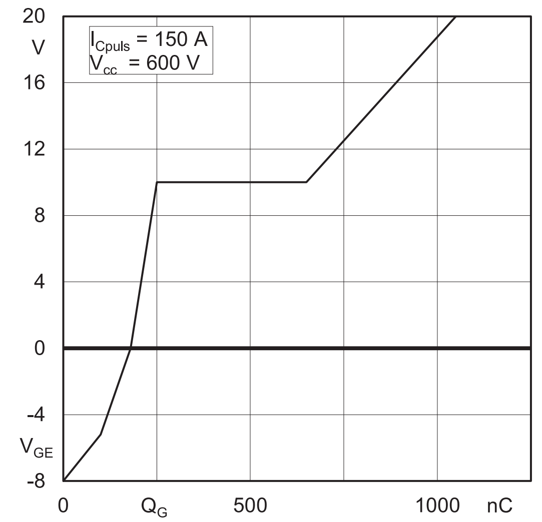


Fig. 6: Typ. gate charge characteristic

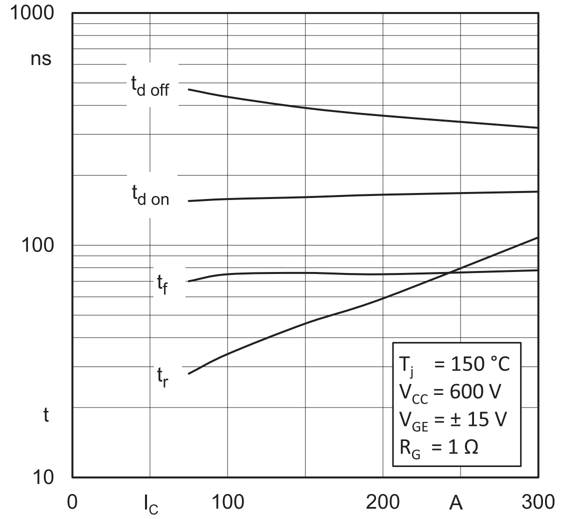


Fig. 7: Typ. switching times vs. I_C

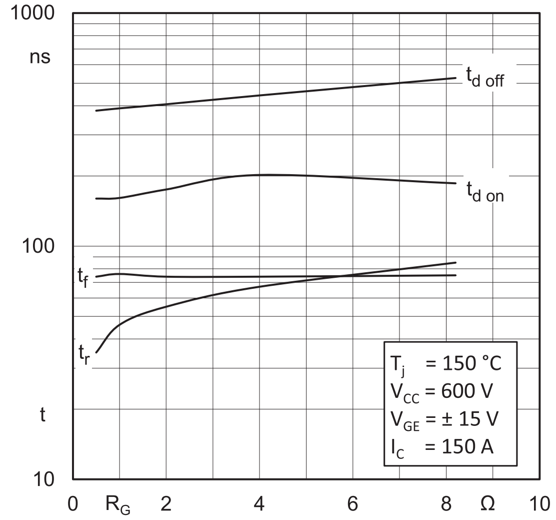


Fig. 8: Typ. switching times vs. gate resistor R_G

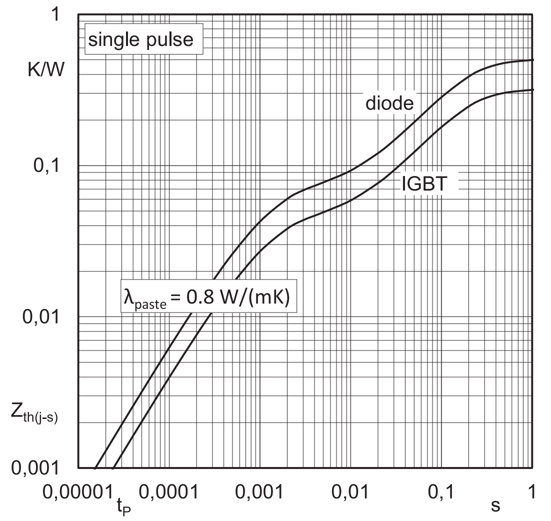


Fig. 9: Transient thermal impedance of IGBT and Diode

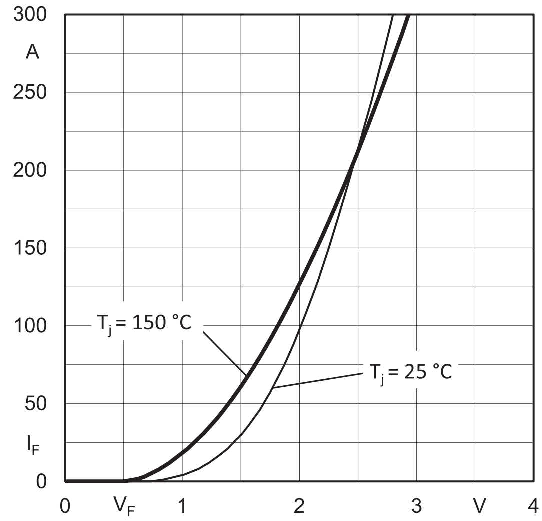


Fig. 10: CAL diode forward characteristic

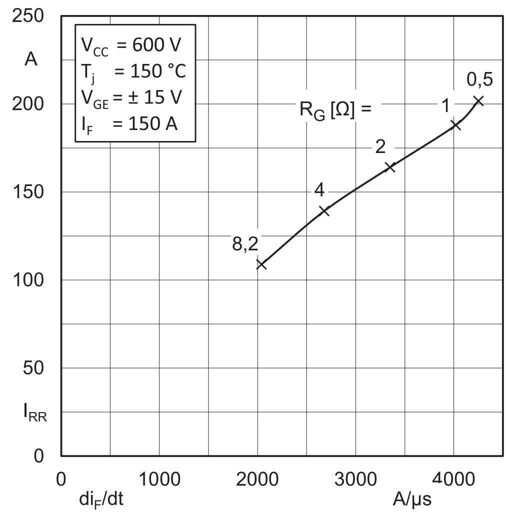


Fig. 11: Typ. CAL diode peak reverse recovery current

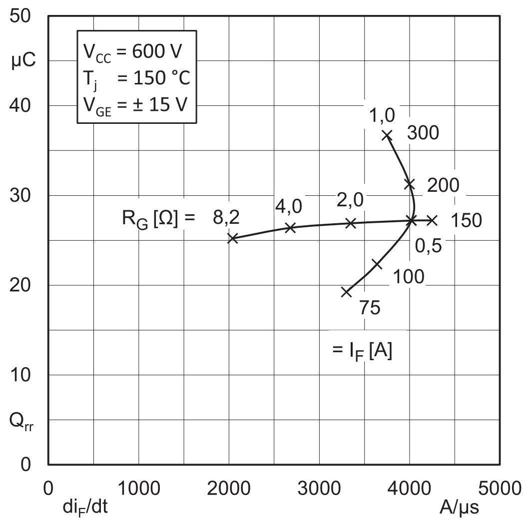
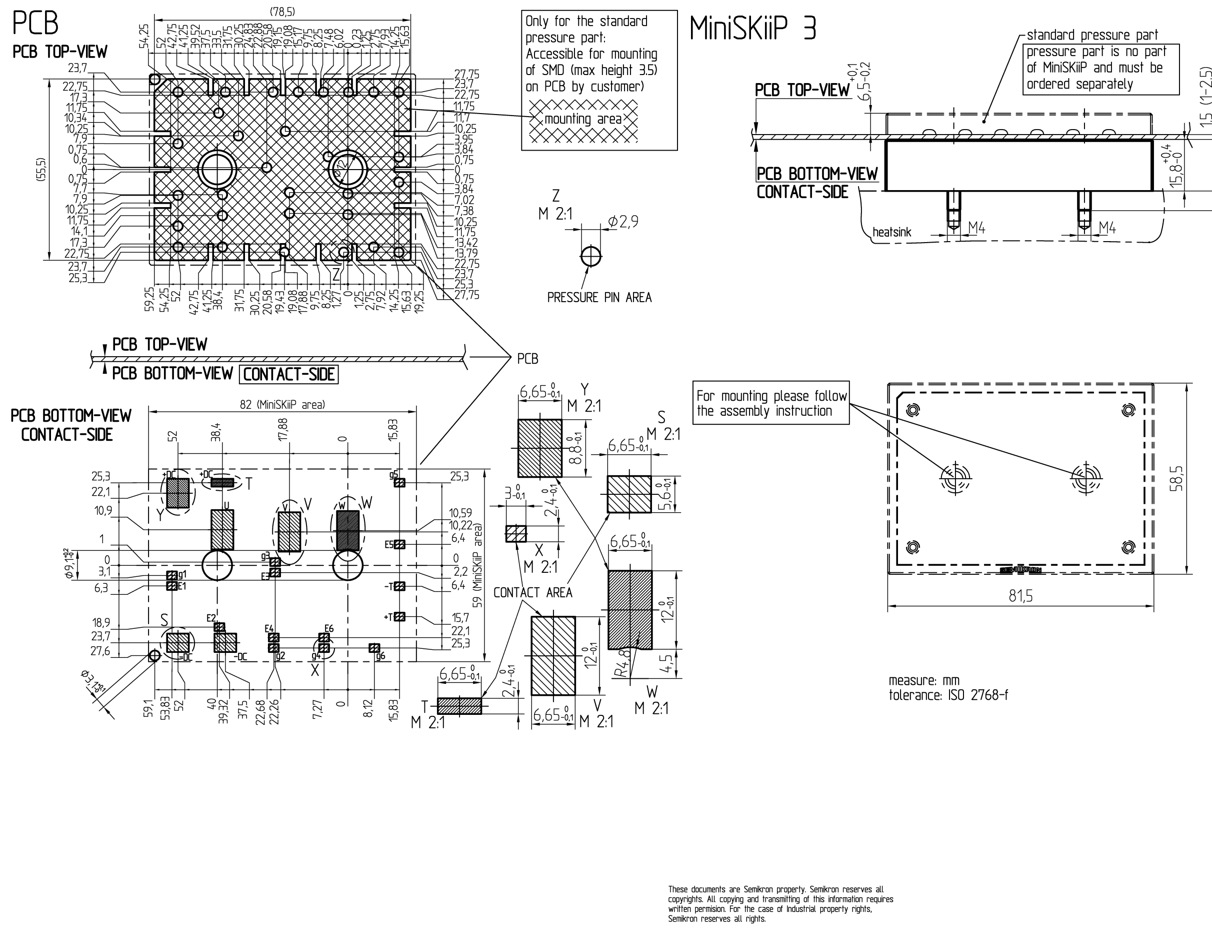
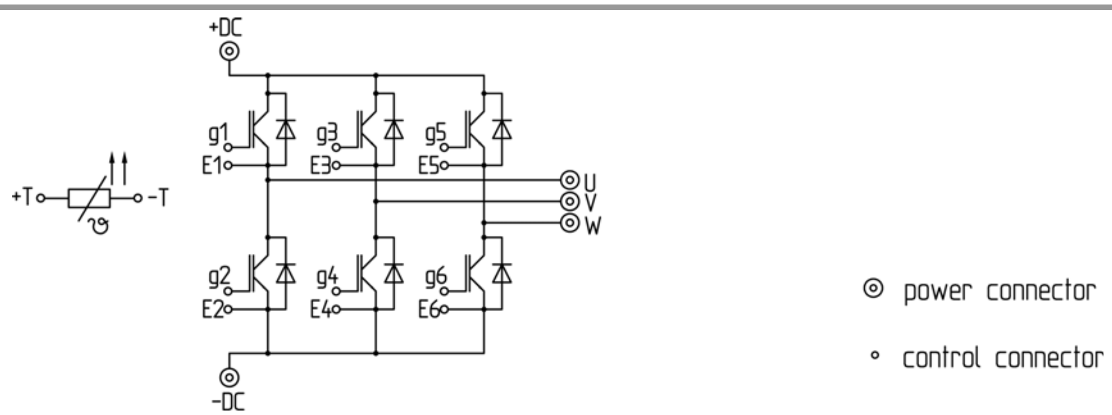


Fig. 12: Typ. CAL diode recovery charge



pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

***IMPORTANT INFORMATION AND WARNINGS**

The specifications of SEMIKRON products may not be considered as guarantee or assurance of product characteristics ("Beschaffenheitsgarantie"). The specifications of SEMIKRON products describe only the usual characteristics of products to be expected in